

T-41-11

CLED400

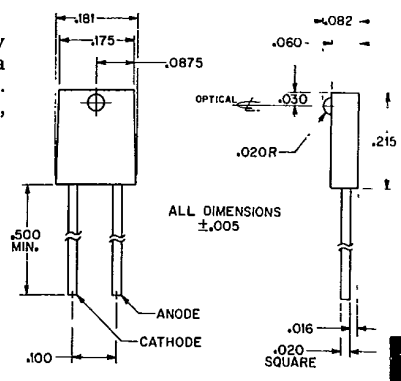
Gallium Arsenide Infrared Emitting Diode

GENERAL DESCRIPTION — The CLED400 is a high intensity infrared emitting diode molded in a clear epoxy package. It has a molded lens to provide a controlled angular irradiance pattern. The CLED400 is spectrally compatible with Clairex CLT4140, CLT4160 phototransistors and CLR4180 photo Darlington.

ABSOLUTE MAXIMUM RATINGS

- Maximum Temperatures
- Storage Temperature - 40°C + 100°C
- Maximum DC Power Dissipation 60mw
- Maximum DC Forward Current 50ma
- *Peak Transient Forward Current 1.5A
- Lead Soldering Temperature 240°C for 3 sec.

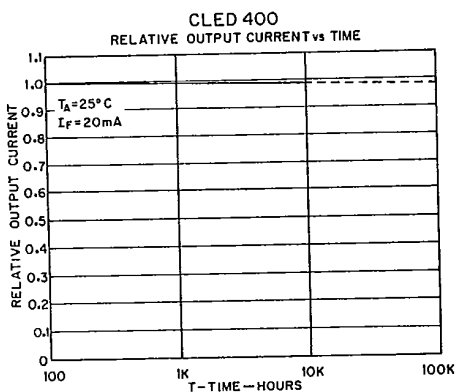
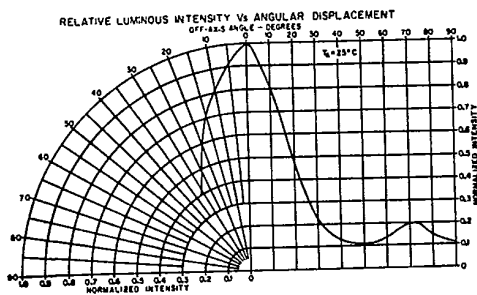
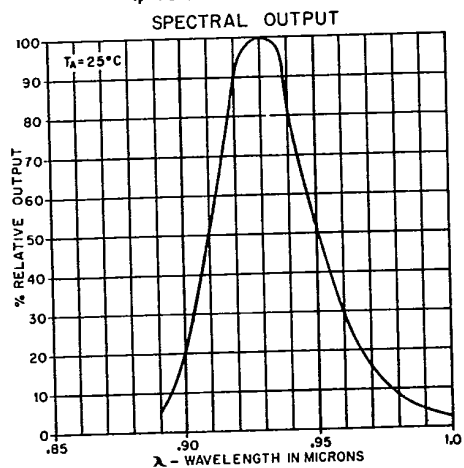
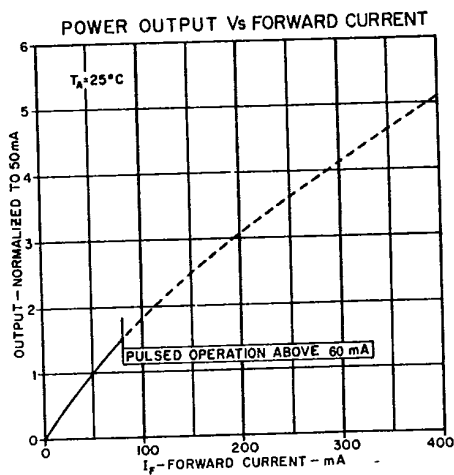
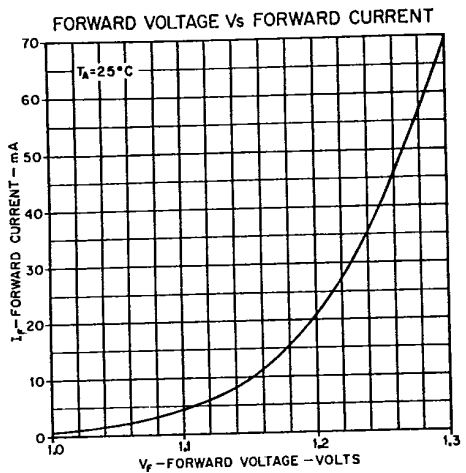
*(Pulse width = 1 μsec, 300 pps)



ELECTRICAL CHARACTERISTICS (25°C Free Air unless otherwise designated.)

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P _o	Output Power	I _f = 50 ma	.5			milliwatts
P _a	On-Line Intensity	I _f = 50 ma	1.5	6		mw/cm ²
λ _{PEAK}	Wave Length			.93		microns
τ _s	Speed of Response	I _f = 20 ma		600		nanosecs
V _F	Forward Voltage	I _f = 20 ma			1.7	volts
BV _R	Reverse Breakdown Voltage	I _R = 10μa	3.0			volts
θ	1/2 Power Angle			20		degrees

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